

# Hyperfast Rectifier, 2 A FRED Pt®

**eSMP® Series  
SMF (DO-219AB)**



Top view

Bottom view

Cathode Anode



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

## FEATURES

- Hyperfast recovery time, reduced  $Q_{rr}$ , and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

## DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use as clamp, snubber and freewheeling diode in a flyback aux power supplies, bootstrap and desaturate for HV MOSFET and IGBT driver, high frequency rectifiers in a cuk and sepic circuit for LED lighting.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

## MECHANICAL DATA

**Case:** SMF (DO-219AB)

Molding compound meets UL 94 V-0 flammability rating

**Terminals:** matte tin plated leads, solderable per J-STD-002

**Polarity:** color band denotes cathode end

## LINKS TO ADDITIONAL RESOURCES



3D Models



Application Notes

PRIMARY CHARACTERISTICS	
$I_{F(AV)}$	2 A
$V_R$	1200 V
$V_F$ at $I_F$	1.60 V
$t_{rr}$	45 ns
$T_J$ max.	175 °C
Package	SMF (DO-219AB)
Circuit configuration	Single

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	$V_{RRM}$		1200	V
Average rectified forward current	$I_{F(AV)}$	$T_{Sp} = 85$ °C, DC conduction	2	A
Non-repetitive peak surge current	$I_{FSM}$	$T_J = 25$ °C, 8.3 ms sine pulse	21	
Operating junction and storage temperatures	$T_J, T_{Stg}$		-55 to +175	°C

ELECTRICAL SPECIFICATIONS ( $T_J = 25$ °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}, V_R$	$I_R = 100$ $\mu$ A	1200	-	-	V
Forward voltage, per diode	$V_F$	$I_F = 2$ A	-	2.0	2.50	
		$I_F = 2$ A, $T_J = 125$ °C	-	1.70	1.95	
		$I_F = 2$ A, $T_J = 150$ °C	-	1.60	1.85	
Reverse leakage current, per diode	$I_R$	$V_R = V_R$ rated	-	-	3	$\mu$ A
		$T_J = 125$ °C, $V_R = V_R$ rated	-	-	30	
Junction capacitance	$C_T$	$V_R = 1200$ V	-	3.5	-	pF

**DYNAMIC RECOVERY CHARACTERISTICS** ( $T_J = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Reverse recovery time	$t_{rr}$	$I_F = 0.5\text{ A}$ , $I_R = 1\text{ A}$ , $I_{rr} = 0.25\text{ A}$	-	35	45	ns
		$T_J = 25\text{ }^{\circ}\text{C}$	-	105	-	
		$T_J = 125\text{ }^{\circ}\text{C}$	-	145	-	
Peak recovery current	$I_{RRM}$	$T_J = 25\text{ }^{\circ}\text{C}$	-	4.0	-	A
		$T_J = 125\text{ }^{\circ}\text{C}$	-	5.0	-	
Reverse recovery charge	$Q_{rr}$	$T_J = 25\text{ }^{\circ}\text{C}$	-	165	-	nC
		$T_J = 125\text{ }^{\circ}\text{C}$	-	315	-	

**THERMAL - MECHANICAL SPECIFICATIONS**

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	$T_J, T_{Stg}$		-55	-	175	$^{\circ}\text{C}$
Thermal resistance, junction to mount	$R_{thJM}^{(1)}$	Device mounted on PCB with 2 x 3.5 mm soldering lands	-	23	26	$^{\circ}\text{C/W}$
Thermal resistance, junction to ambient	$R_{thJA}$	Device mounted on PCB with recommended pad size	-	125	-	$^{\circ}\text{C/W}$
Approximate weight			0.015			g
Marking device		Case style SMF (DO-219AB)	MSX			

**Note**

(1) Thermal resistance junction to mount follows JEDEC® 51-14 transient dual interface test method (TDIM)

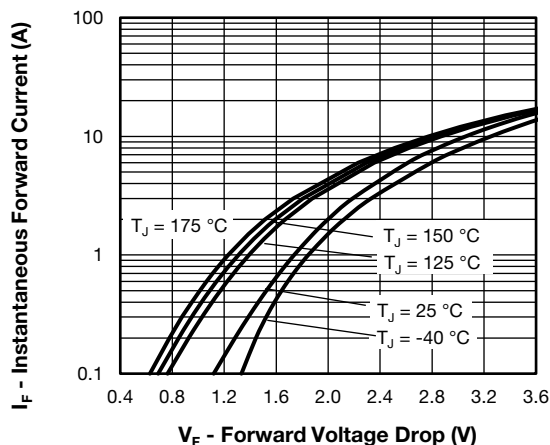


Fig. 1 - Typical Forward Voltage Drop Characteristics

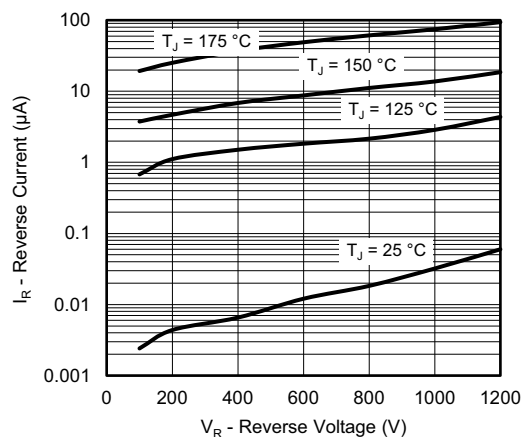


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

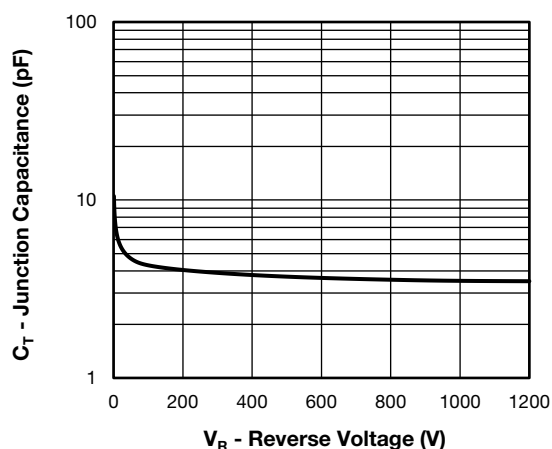


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

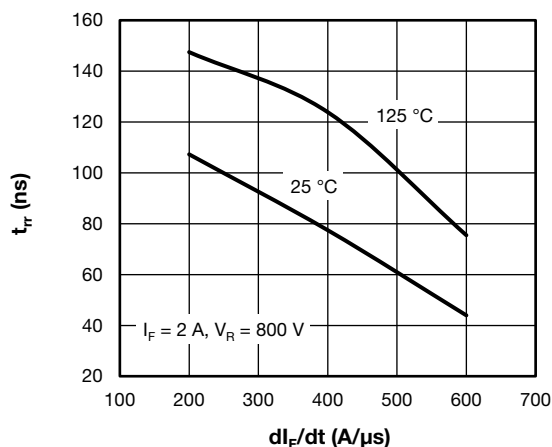
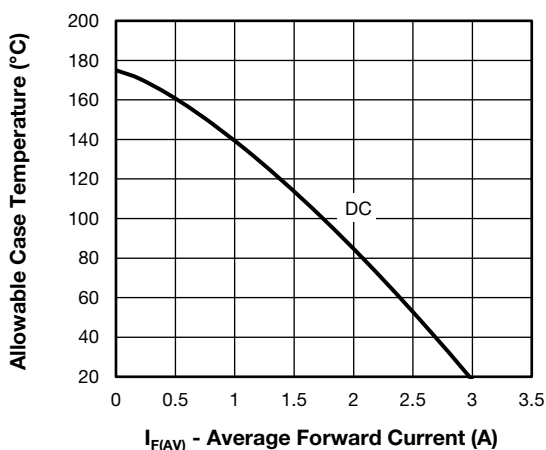

Fig. 6 - Typical Reverse Recovery Time vs.  $dI_F/dt$ 


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

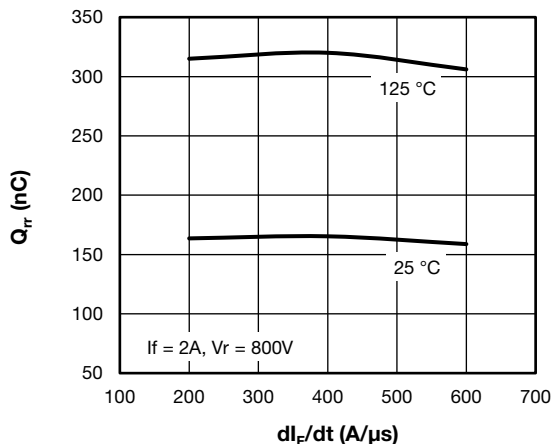
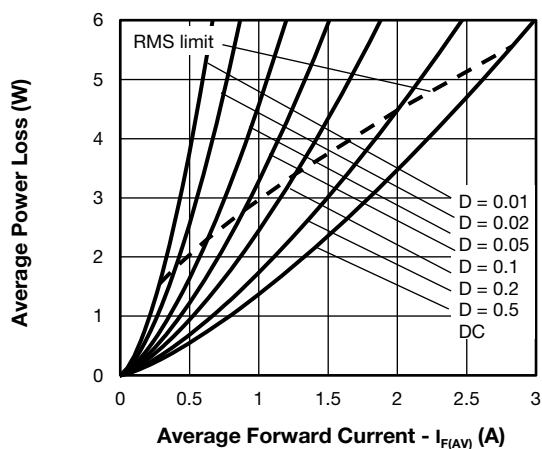
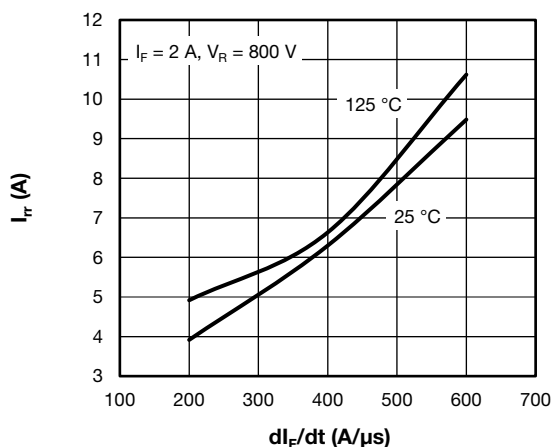

Fig. 7 - Typical Stored Charge vs.  $dI_F/dt$ 


Fig. 5 - Forward Power Loss Characteristics


Fig. 8 -  $I_{rr}$  (A) vs.  $dI_F/dt$ 
**Note**

- (1) Formula used:  $T_C = T_J - (P_d + P_{dREV}) \times R_{thJC}$ ;  
 $P_d$  = forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 5);  
 $P_{dREV}$  = inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = rated  $V_R$

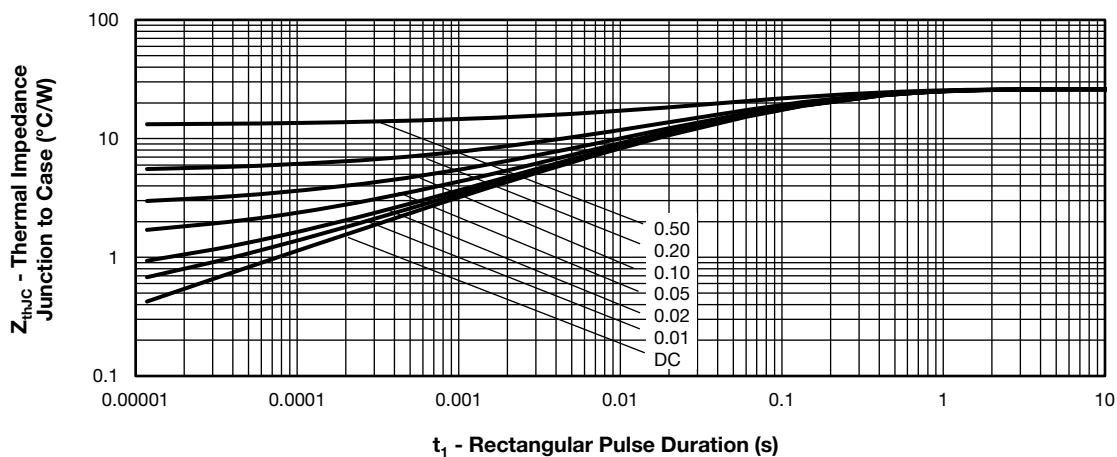


Fig. 9 - Transient Thermal Impedance, Junction to Case

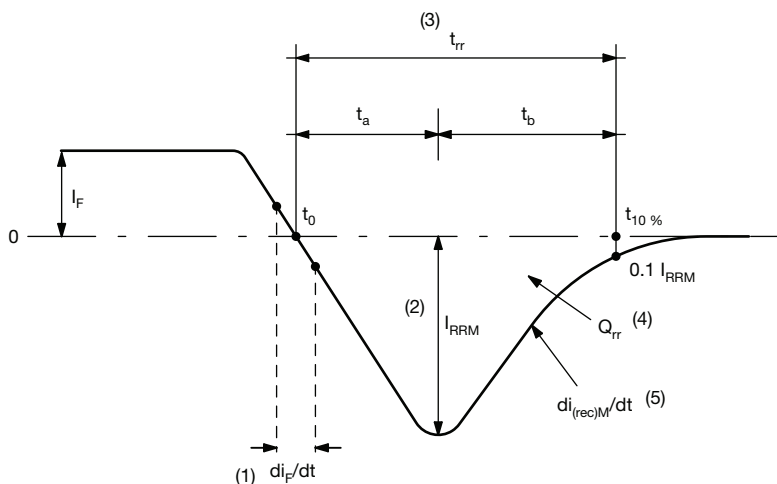


Fig. 10 - Reverse Recovery Waveform and Definitions

#### Notes

- (1)  $di_F/dt$  - rate of change of current through zero crossing
- (2)  $I_{RRM}$  - peak reverse recovery current
- (3)  $t_{rr}$  - reverse recovery time measured from  $t_0$ , crossing point of negative going  $I_F$ , to point  $t_{10\%}$ ,  $0.1 I_{RRM}$
- (4)  $Q_{rr}$  - area under curve defined by  $t_0$  and  $t_{10\%}$ 

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t) dt$$
- (5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$

**ORDERING INFORMATION TABLE**

Device code	<b>VS-</b>	<b>E</b>	<b>7</b>	<b>F</b>	<b>X</b>	<b>02</b>	<b>12</b>	<b>-M3</b>
	1	2	3	4	5	6	7	8
	1	-	Vishay Semiconductors product					
	2	-	Circuit configuration: E = single diode					
	3	-	7 = FRED generation 7					
	4	-	F = SMF package					
	5	-	Process type, X = hyperfast recovery					
	6	-	Current rating (02 = 2 A)					
	7	-	Voltage code (12 = 1200 V)					
	8	-	-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free					

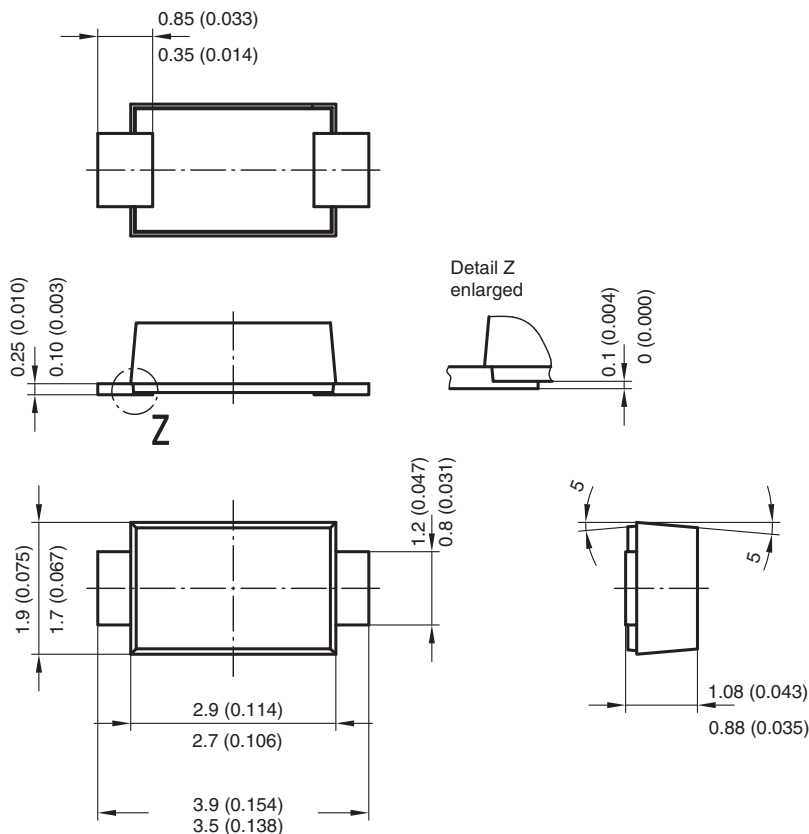
<b>ORDERING INFORMATION</b> (Example)			
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-E7FX0212-M3/I	10 000	10 000	13" diameter plastic tape and reel

<b>LINKS TO RELATED DOCUMENTS</b>	
Dimensions	<a href="http://www.vishay.com/doc?95572">www.vishay.com/doc?95572</a>
Part marking information	<a href="http://www.vishay.com/doc?95618">www.vishay.com/doc?95618</a>
Packaging information	<a href="http://www.vishay.com/doc?95577">www.vishay.com/doc?95577</a>
SPICE model	<a href="http://www.vishay.com/doc?97265">www.vishay.com/doc?97265</a>

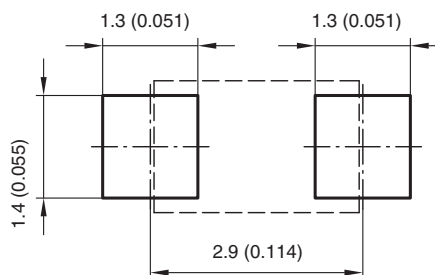


## SMF (DO-219AB)

**DIMENSIONS** in millimeters (inches)



Foot print recommendation:



Created - Date: 15. February 2005  
Rev. 3 - Date: 13. March 2007  
Document no.:S8-V-3915.01-001 (4)  
17247



## Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.